



E. Compound Semiconductors 분과

2021년 1월 27일(수), 09:00-10:30 / 채널 C

[WC1-E] Compound Semiconductors I

좌장: 장우진 박사 (ETRI)

<p>WC1-E-1 09:00-09:15</p>	<p>$L_g = 19$ nm $\text{In}_{0.8}\text{Ga}_{0.2}\text{As}$ Composite-Channel High-Electron Mobility Transistors with Record $f_T = 738$ GHz</p> <p>Hyeon-Bhin Jo¹, Seung-Won Yun¹, Jun-Gyu Kim¹, Dae-Hyun Kim¹, Takuya Tsutsumi², Hiroki Sugiyama², and Hideaki Matsuzaki²</p> <p>¹School of Electronic and Electrical Engineering, Kyungpook National University, ²NTT Device Technology Laboratories</p>
<p>WC1-E-2 09:15-09:30</p>	<p>High Breakdown Voltage and Low Current Dispersion in AlGaIn/GaN HEMTs with High Quality AlN Buffer Layer</p> <p>Jeong-Gil Kim¹, Chuyoung Cho², Eunjin Kim¹, Jae Seok Hwang², Kyung-Ho Park², and Jung-Hee Lee¹</p> <p>¹School of Electronic and Electrical Engineering, Kyungpook national university ²KANC</p>
<p>WC1-E-3 09:30-09:45</p>	<p>High-Frequency InGaAs-On-Insulator HEMTs for Monolithic 3D Integrated RF Applications</p> <p>Jaeyong Jeong¹, Seong Kwang Kim¹, Jongmin Kim³, Dae-Myeong Geum¹, Juyeong Park², Jae-Hyung Jang², and Sanghyeon Kim¹</p> <p>¹School of Electrical Engineering, KAIST, ²School of Electrical Engineering and Computer Science, GIST, ³Division of Device Technology, KANC</p>
<p>WC1-E-4 09:45-10:00</p>	<p>Growth and Characterization of AlGaIn/GaN/AlN Double-Hetero Structure High Electron Mobility Transistors with Si-doped GaN insert layer Grown on Sapphire Substrate by HT-MOCVD</p> <p>Minho Kim, Uiho Choi, Donghyeop Jung, Keono Kim, and Okhyun Nam</p> <p>Department of Nano Optical Engineering, Korea Polytechnic University</p>
<p>WC1-E-5 10:00-10:15</p>	<p>High Performances of AlGaIn/GaN MISHEMTs on Silicon with In-situ SiN Passivation Layer</p> <p>Seung-Hyeon Kang, Jeong-Gil Kim, Quan Dai, Terirama Thingujam, Woo-Hyun Ahn, Eun-Jin Kim, and Jung-Hee Lee</p> <p>School of Electronics Engineering, Kyungpook National University</p>
<p>WC1-E-6 10:15-10:30</p>	<p>Suppression of Short Channel Effect in GaN Vertical GAA for Low-voltage Application</p> <p>Terirama Thingujam, Quan Dai, Woo-Hyun Ahn, Seung-Hyeon Kang, and Jung-Hee Lee</p> <p>School of Electrical and Electronics Engineering, Kyungpook National University</p>

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